


Please type a plus sign (+) inside this box. FORM PTO/SB/08

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	Unassigned
				Filing Date	Filed Herewith
				First Named Inventor	Richard A. Blanchard
				Group Art Unit	2811
				Examiner Name	Unassigned
				Attorney Docket Number	GS 124 D1
Sheet	1	of	2		

[illegible]

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office ¹	Number	Class/ Subclass			
Examiner Signature					Date Considered	6/25/04	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

Substitute for form 1449A/PTO				Complete if Known	
				Application Number	Unassigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	Filed Herewith
				First Named Inventor	Richard A. Blanchard
(use as many sheets as necessary)				Group Art Unit	2811
				Examiner Name	Unassigned
Sheet	2	of	2	Attorney Docket Number	GS 124 D1

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TJN	1	Baliga, B. Jayant, Chapter 7, "Power Mosfet: 7.1 Basic Structure and Operation," PWS Publishing (Boston, 1996), pp. 336-339.	
	2	Wolf, Stanley et al., "Silicon Processing for the VLSI Era", Vol. 1: Process Technology," Lattice Press, Sunset Beach, CA, (1986), pp. 321-323.	
	3	Wilson, Syd R., et al., "Handbook of Multilevel Metallization for Integrated Circuits," Noyes Publ., Westwood, New Jersey, (1993), pp. 42-59; 867-872.	
	4	IBM Technical Disclosure Bulletin, "Fabrication of Narrow Self Aligned Trenches and Isolated N-Type Silicon Region With buried N+ Layer," Vol. 34, No. 10A, (March, 1992), pp. 397-399.	
	5	Gary E. McGuire, "Semiconductor Materials and Process Technology Handbook," Noyes Publ., Norwich, New York, (1988), p.18.	
	6	Hu, Chenning, "Optimum Doping Profile for Minimum Ohmic Resistance and High-Breakdown Voltage," IEEE Transactions on Electron Devices, Vol. ED-26, No. 3, March 1979, pp. 243-244.	
TJN	7	Grove, A. S., Physics and Technology of Semiconductor Devices, 3.7, "The Redistribution of Impurities in Epitaxial Growth," pp. 78-83, John Wiley and Sons, Inc. New York, 1967.	

Examiner Signature		Date Considered	6/12/04
-----------------------	--	--------------------	---------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English Language Translation is attached.